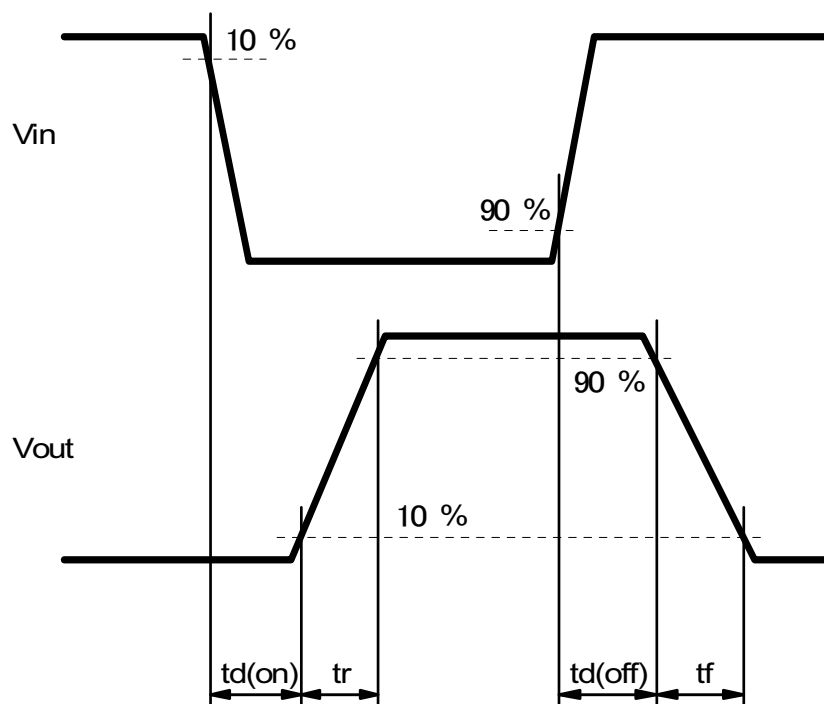
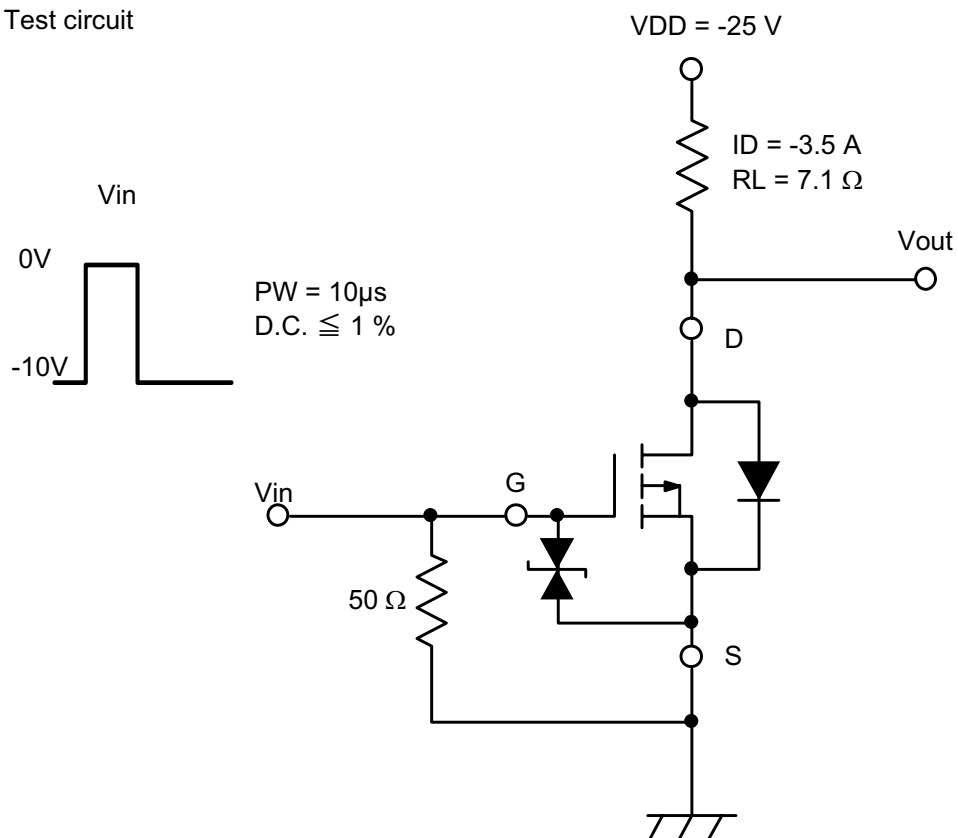


Product Specification Type Number : M T M 9 8 1 4 0 0 B B F *1					Prepared by S.Miyata	Checked by M.Fujisawa	Applied by H.Shidooka	Established by K.Kemichi	
Type	Silicon Field Effect Transistors								
Application	Switching								
Structure	P-Channel MOS Type								
Outline	SO8-F1-B					Marking		BA	
Absolute Maximum Ratings	VDSS (V)	VGSS (V)	ID (A)	IDp (A)	PD ^{*2} (W)	Tch (°C)	Tstg -55 to +150 (°C)		
	-40	±20	-7	-28	2	150			
Electrical characteristics (Ta = 25 °C ±3 °C)									
Item	Symbol	Measuring condition	Limit			Unit			
			min.	typ.	max.				
Drain-Source Voltage	VDSS	ID = -1 mA, VGS = 0 V	-40			V			
Drain-Source Cutoff Current	IDSS	VDS = -40 V, VGS = 0 V			-10	μA			
Gate-Source Cutoff Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μA			
Gate Threshold Voltage	Vth	ID = -1.0 mA, VDS = -10.0 V	-1.0		-2.5	V			
Drain Resistance (ON)	^{*3} RDS(ON)	ID = -7 A, VGS = -10 V		19	25	mΩ			
Drain Resistance (ON)	^{*3} RDS(ON)	ID = -3.5A, VGS = -4.5V		28	45	mΩ			
Forward Transfer Admittance	^{*3} Yfs	ID = -7 A, VDS = -10 V	10			S			
Small-Signal Short-Circuit Input Capacitance	Ciss	VDS = -10 V, VGS = 0 V, f = 1MHz		2700		pF			
Small-Signal Short-Circuit Output Capacitance	Coss	VDS = -10V, VGS = 0V, f = 1MHz		190		pF			
Small-Signal Reverse Transfer Capacitance	Crss	VDS = -10 V, VGS = 0 V, f = 1 MHz		175		pF			
Turn-on Delay Time	^{*3,4} td(on)	VDD = -25 V, VGS = 0 to -10 V, ID = -3.5 A		18		ns			
Rise Time	^{*3,4} tr	VDD = -25 V, VGS = 0 to -10 V, ID = -3.5 A		15		ns			
Turn-off Delay Time	^{*3,4} td(off)	VDD = -25 V, VGS = -10 to 0 V, ID = -3.5 A		230		ns			
Fall Time	^{*3,4} tf	VDD = -25 V, VGS = -10 to 0 V, ID = -3.5 A		70		ns			
Note: Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.									
*1 Packing Embossed type (thermo-compressioon sealing) *2 Measuring on ceramic board at 50×50×1.0mm. *3 Pulse test *4 See test circuit Internally connected circuit 1.Source 2.Source 3.Source 4.Gate 5.Drain 6.Drain 7.Drain 8.Drain									
2008.01.31									
Established	Revised								

Product Specification

Type Number : M T M 9 8 1 4 0 0 B B F
*1

Test circuit



2008.01.31

Established

Revised